

ACT108-600E

AC Thyristor power switch

Rev. 01 — 1 September 2009

Product data sheet

1. Product profile

1.1 General description

AC Thyristor power switch in a SOT54 plastic package

1.2 Features and benefits

- Exclusive negative gate triggering
- Full cycle AC conduction
- High over-voltage withstand capability
- Remote gate separates the gate driver from the effects of the load current
- Very high noise immunity

1.3 Applications

- Fan motor circuits
- Lower-power highly inductive, resistive and safety loads
- Pump motor circuits

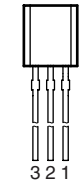
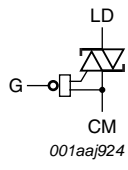
1.4 Quick reference data

Table 1. Quick reference

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	-	600	V
I_{GT}	gate trigger current	$V_{\text{D}} = 12 \text{ V}$; $I_{\text{T}} = 100 \text{ mA}$; LD+ G-; $T_{\text{j}} = 25 \text{ }^{\circ}\text{C}$; see Figure 6	1	-	10	mA
		$V_{\text{D}} = 12 \text{ V}$; $I_{\text{T}} = 100 \text{ mA}$; LD- G-; $T_{\text{j}} = 25 \text{ }^{\circ}\text{C}$	1	-	10	mA
$I_{\text{T(RMS)}}$	RMS on-state current	full sine wave; $T_{\text{lead}} \leq 71 \text{ }^{\circ}\text{C}$; see Figure 1	-	-	0.8	A
V_{CL}	clamping voltage	$I_{\text{CL}} = 100 \text{ mA}$; $t_{\text{p}} = 1 \text{ ms}$; $T_{\text{j}} \leq 125 \text{ }^{\circ}\text{C}$; see Figure 13	650	-	-	V
V_{PP}	peak pulse voltage	$T_{\text{j}} = 25 \text{ }^{\circ}\text{C}$; non-repetitive, off-state; see Figure 4	-	-	2	kV
V_{T}	on-state voltage	$I_{\text{T}} = 1.1 \text{ A}$; see Figure 9	-	-	1.3	V

2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	CM	common	 <p>SOT54 (TO-92)</p>	 <p>001aaJ924</p>
2	G	gate		
3	LD	load		

3. Ordering information

Table 3. Ordering information

Type number	Package		Version
	Name	Description	
ACT108-600E	TO-92	plastic single-ended leaded (through hole) package; 3 leads	SOT54

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	600	V
$I_{T(RMS)}$	RMS on-state current	full sine wave; $T_{lead} \leq 71\text{ °C}$; see Figure 1	-	0.8	A
I_{TSM}	non-repetitive peak on-state current	full sine wave; $T_{j(init)} = 25\text{ °C}$; $t_p = 16.7\text{ ms}$	-	8.8	A
		full sine wave; $T_{j(init)} = 25\text{ °C}$; $t_p = 20\text{ ms}$; see Figure 2 and 3	-	8	A
I^2t	I^2t for fusing	$t_p = 10\text{ ms}$; sine-wave pulse	-	0.32	A ² s
di_T/dt	rate of rise of on-state current	$I_T = 1\text{ A}$; $I_G = 20\text{ mA}$; $di_G/dt = 0.2\text{ A}/\mu\text{s}$	-	100	A/ μs
I_{GM}	peak gate current		-	1	A
V_{GM}	peak gate voltage		-	15	V
$P_{G(AV)}$	average gate power		-	0.1	W
T_{stg}	storage temperature		-40	150	°C
T_j	junction temperature		-	125	°C
V_{PP}	peak pulse voltage	$T_j = 25\text{ °C}$; non-repetitive, off-state; see Figure 4	-	2	kV

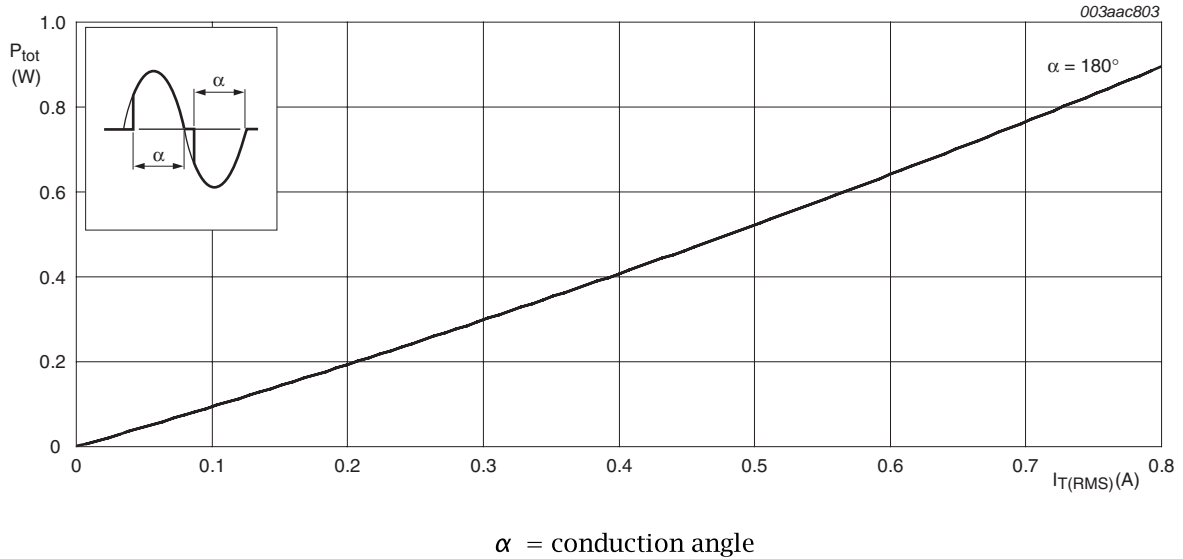


Fig 1. Total power dissipation as a function of RMS on-state current; maximum values

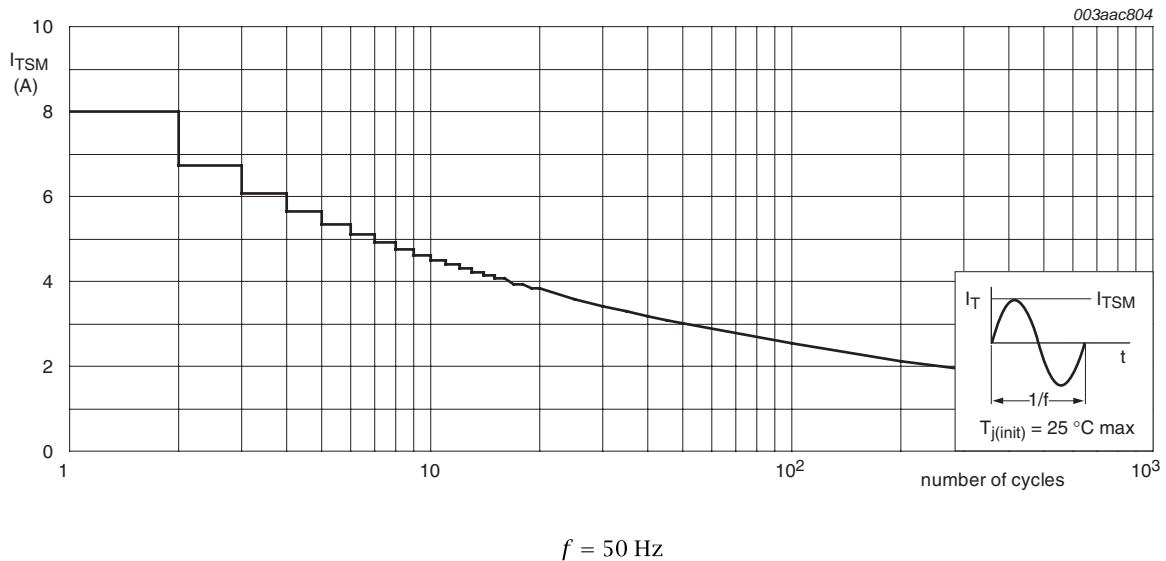
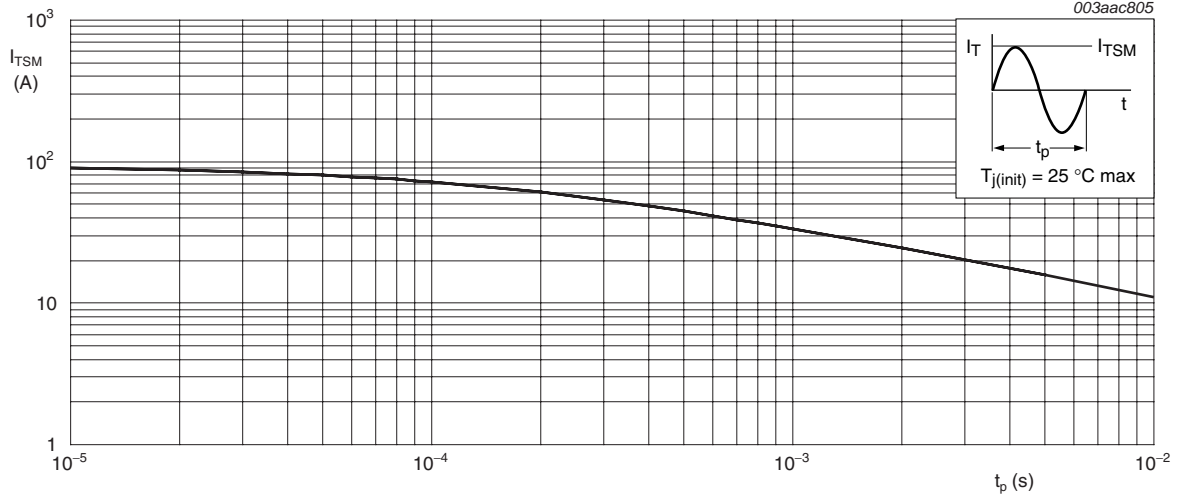


Fig 2. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values



$t_p \leq 20\text{ ms}$

Fig 3. Non-repetitive peak on-state current as a function of pulse width; maximum values

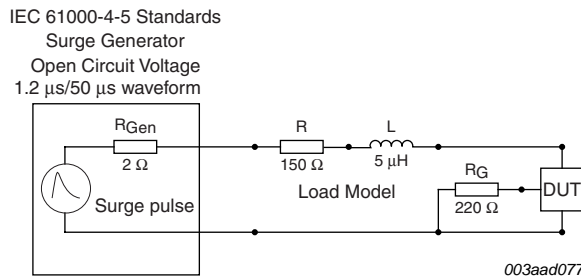


Fig 4. Test circuit for inductive and resistive loads with conditions equivalent to IEC 61000-4-5

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-lead)}$	thermal resistance from junction to lead	full cycle with heatsink compound; see Figure 5	-	-	60	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient		-	150	-	K/W

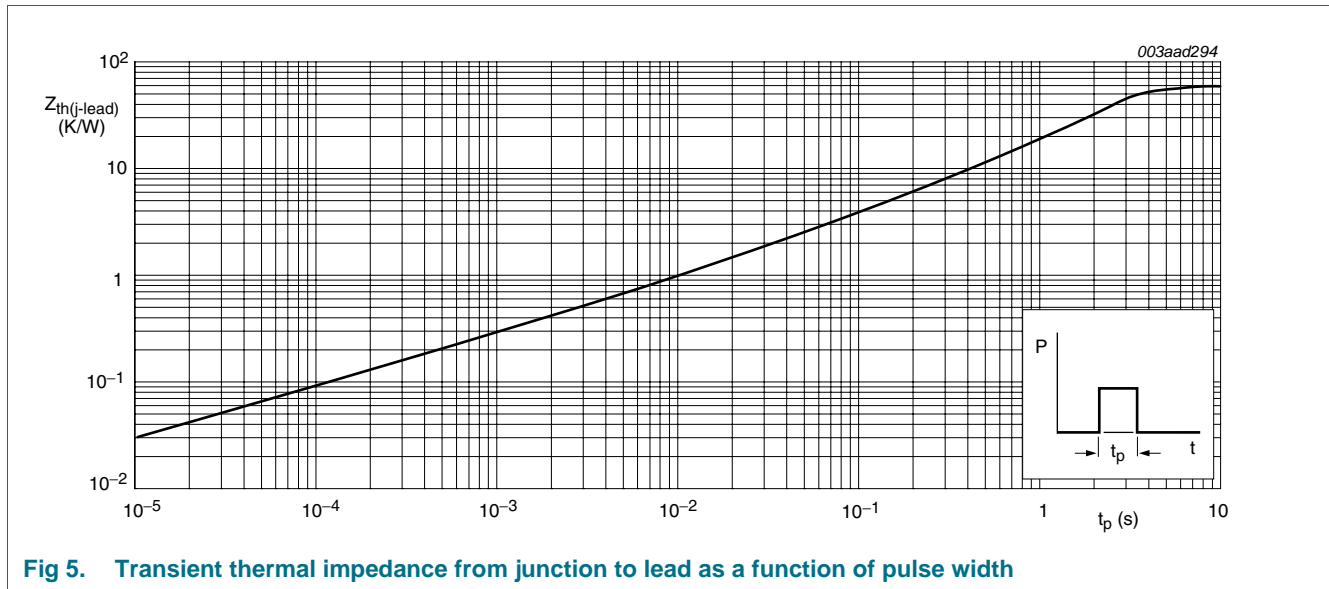
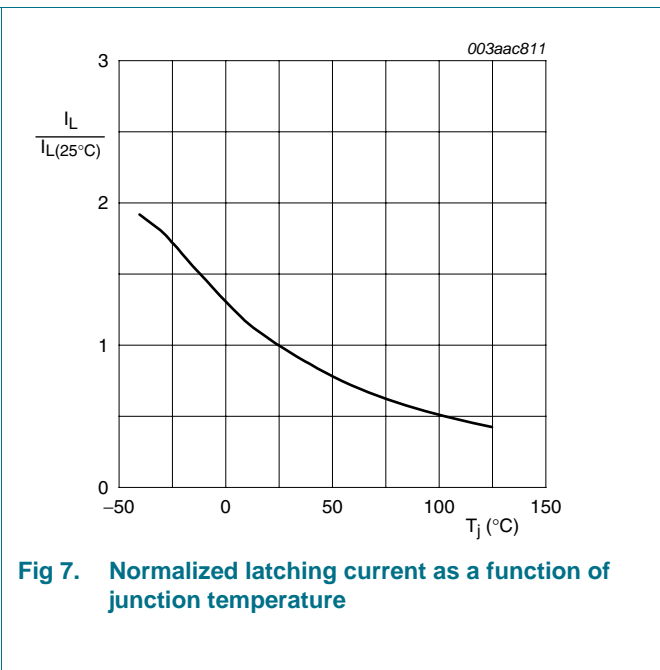
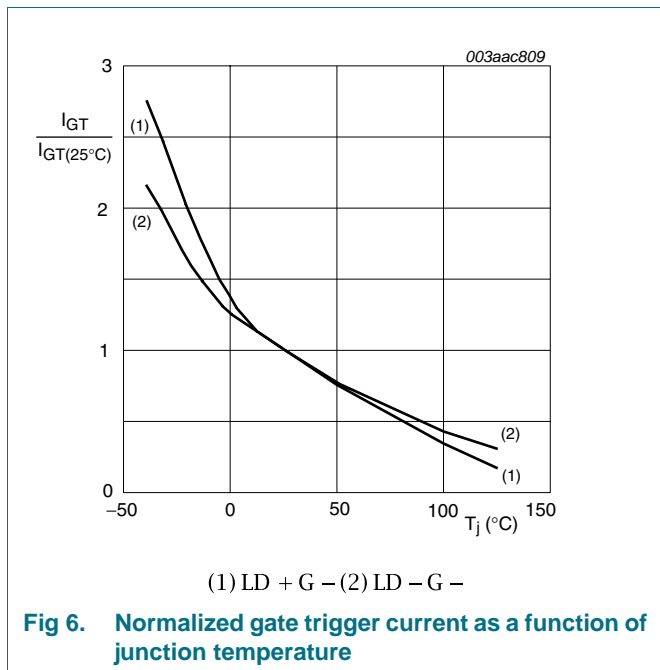


Fig 5. Transient thermal impedance from junction to lead as a function of pulse width

6. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
I_{GT}	gate trigger current	$V_D = 12\text{ V}; I_T = 100\text{ mA}; \text{LD+ G-}; T_j = 25\text{ }^\circ\text{C};$ see Figure 6	1	-	10	mA
		$V_D = 12\text{ V}; I_T = 100\text{ mA}; \text{LD- G-}; T_j = 25\text{ }^\circ\text{C}$	1	-	10	mA
I_L	latching current	$V_D = 12\text{ V}; I_G = 12\text{ mA}; T_j = 25\text{ }^\circ\text{C};$ see Figure 7	-	-	30	mA
I_H	holding current	$V_D = 12\text{ V}; T_j = 25\text{ }^\circ\text{C};$ see Figure 8	-	9	25	mA
V_T	on-state voltage	$I_T = 1.1\text{ A};$ see Figure 9	-	-	1.3	V
V_{GT}	gate trigger voltage	$V_D = 600\text{ V}; I_T = 100\text{ mA}; T_j \leq 125\text{ }^\circ\text{C}$	0.15	-	-	V
		$V_D = 600\text{ V}; I_T = 100\text{ mA}; T_j = 25\text{ }^\circ\text{C}$	-	-	1	V
I_D	off-state current	$V_D = 600\text{ V}; T_j \leq 125\text{ }^\circ\text{C}$	-	-	0.2	mA
		$V_D = 600\text{ V}; T_j \leq 25\text{ }^\circ\text{C}$	-	-	2	μA
dV_D/dt	rate of rise of off-state voltage	$V_{DM} = 402\text{ V}; T_j = 125\text{ }^\circ\text{C};$ gate open circuit; see Figure 10	1000	-	-	$\text{V}/\mu\text{s}$
dI_{com}/dt	rate of change of commutating current	$V_D = 400\text{ V}; T_j = 125\text{ }^\circ\text{C}; I_{T(RMS)} = 1\text{ A};$ $dV_{com}/dt = 15\text{ V}/\mu\text{s};$ gate open circuit; see Figure 11 and 12	0.3	-	-	A/ms
V_{CL}	clamping voltage	$I_{CL} = 100\text{ mA}; t_p = 1\text{ ms}; T_j \leq 125\text{ }^\circ\text{C};$ see Figure 13	650	-	-	V



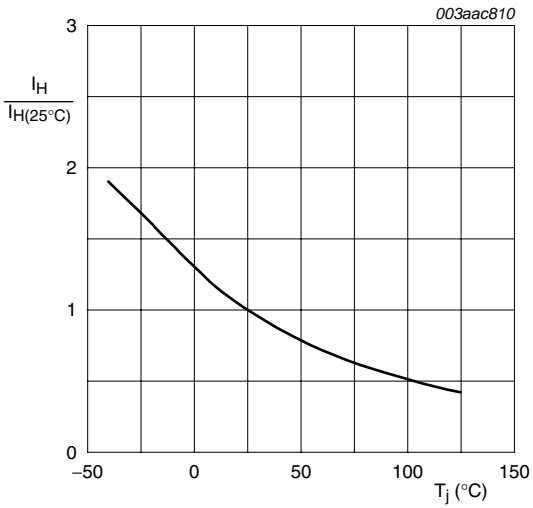
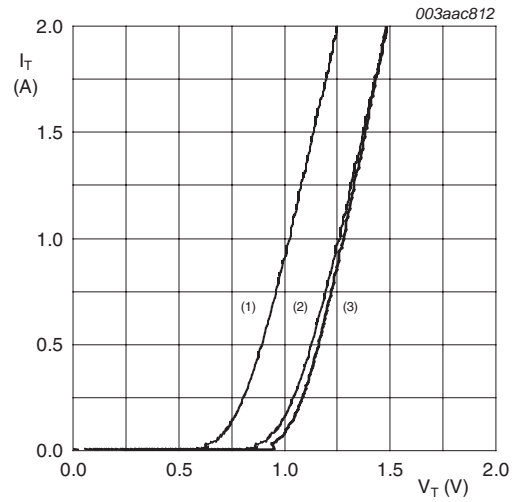
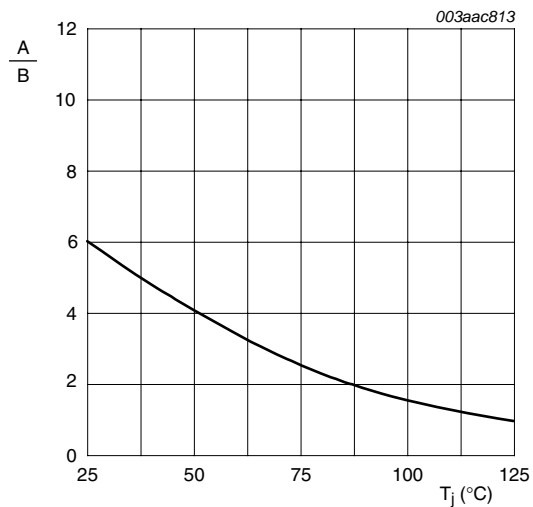


Fig 8. Normalized holding current as a function of junction temperature



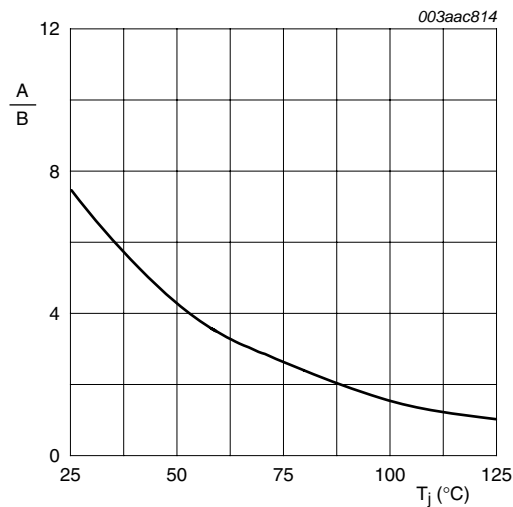
$V_o = 1.043 \text{ V}; R_s = 0.239 \Omega$
 (1) $T_j = 125 \text{ }^\circ\text{C}$; typical values
 (2) $T_j = 125 \text{ }^\circ\text{C}$; maximum values
 (3) $T_j = 25 \text{ }^\circ\text{C}$; maximum values

Fig 9. On-state current as a function of on-state voltage



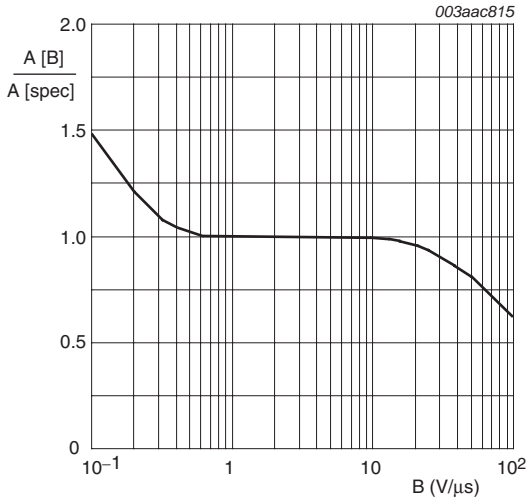
A is dV_D/dt at condition $T_j \text{ }^\circ\text{C}$
 B is dV_D/dt at condition $T_j = 125 \text{ }^\circ\text{C}$

Fig 10. Normalized rate of rise of off-state voltage as a function of junction temperature



A is dI_{com}/dt at condition $T_j \text{ }^\circ\text{C}$
 B is dI_{com}/dt at $T_j = 125 \text{ }^\circ\text{C}$ $V_D = 400 \text{ V}$

Fig 11. Normalized critical rate of rise of commutating current as a function of junction temperature



$A[B]$ is $\frac{dI_{com}}{dt}$ at condition B, $\frac{dV_{com}}{dt}$

$A[spec]$ is the specified data sheet value of $\frac{dI_{com}}{dt}$

Fig 12. Normalized critical rate of change of commutating current as a function of critical rate of change of commutating voltage; minimum values

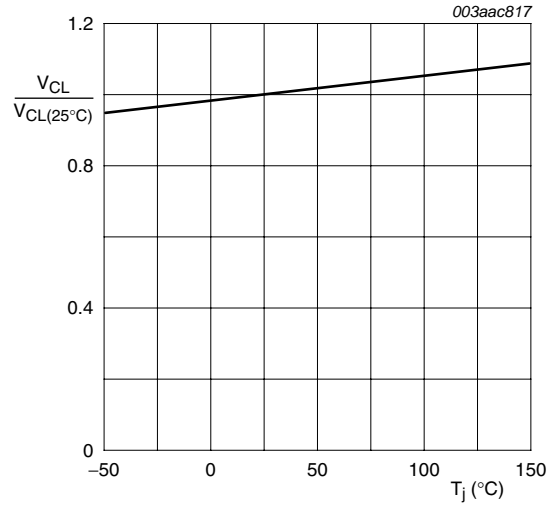


Fig 13. Normalized clamping voltage (upper limit) as a function of junction temperature; minimum values

7. Package outline

Plastic single-ended leaded (through hole) package; 3 leads

SOT54

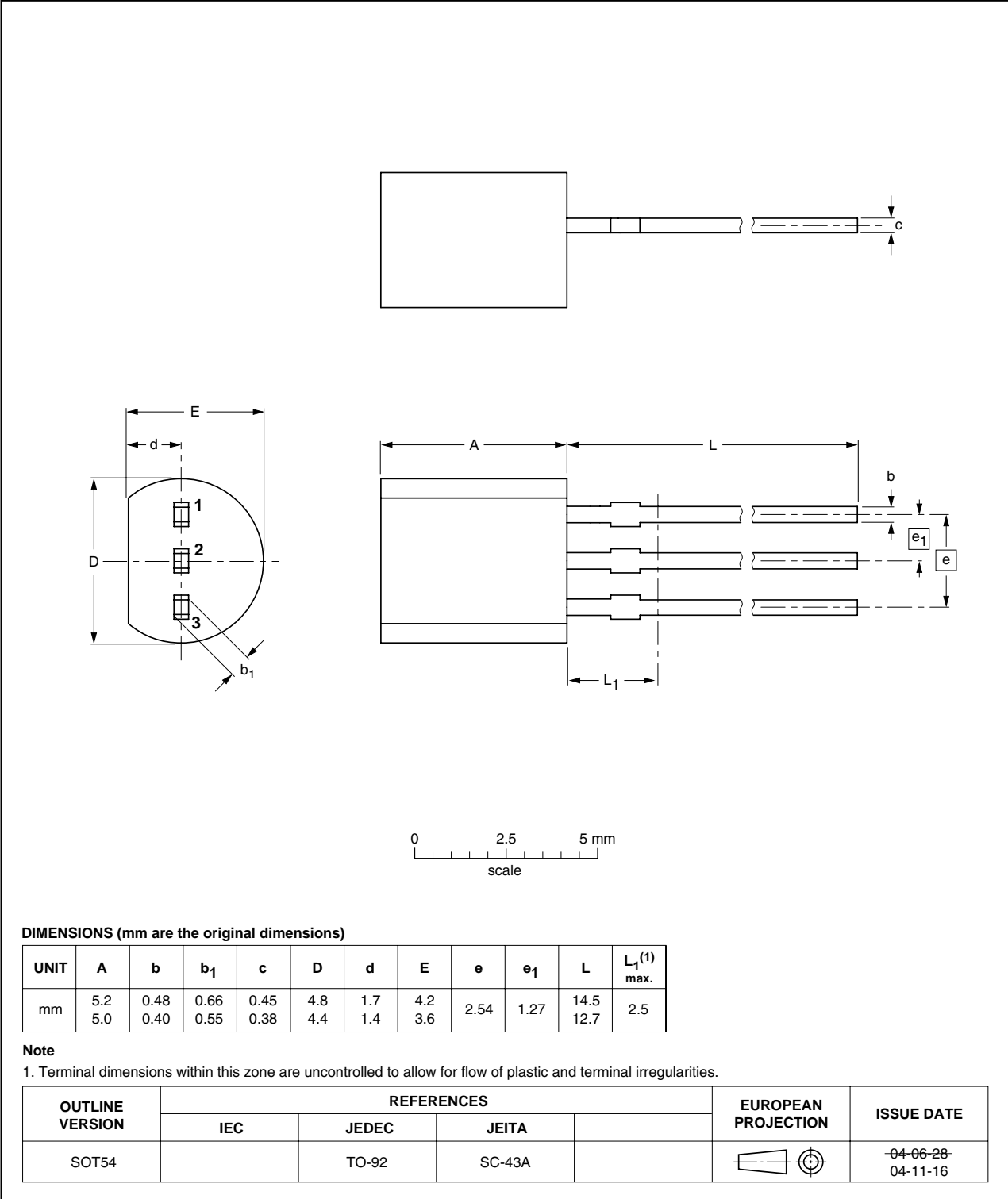


Fig 14. Package outline SOT54 (TO-92)

8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
ACT108-600E_1	20090901	Product data sheet	-	-

9. Legal information

9.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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